

SiC JFET Division

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Rev. C, Jan 2025





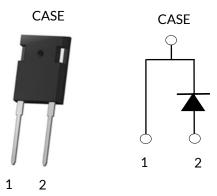
Silicon Carbide (SiC) Diode - EliteSiC, TO-247-2L, 10 A, 1200 V SiC Merged







UJ3D1210K2



Description UnitedSiC offers the 3rd generation of high perform PiN-Schottky (MPS) diodes. With zero reverse reserves

PiN-Schottky (MPS) Diode

UnitedSiC offers the 3^{rd} generation of high performance SiC Merged-PiN-Schottky (MPS) diodes. With zero reverse recovery charge and 175° C maximum junction temperature, these diodes are ideally suited for high frequency and high efficiency power systems with minimum cooling requirements.

Features

- Maximum operating temperature of 175°C
- Easy paralleling
- Extremely fast switching not dependent on temperature
- No reverse or forward recovery
- Enhanced surge current capability, MPS structure
- 100% UIS tested
- AEC-Q101 qualified
- AECQ Qualified

Part Number	Package	Marking
UJ3D1210K2	TO-247-2L	UJ3D1210K2







Typical applications

- Power converters
- Industrial motor drives
- Switch mode power supplies
- Power factor correction modules













Maximum Ratings

Parameter	Symbol	Test Conditions	Value	Units	
DC blocking voltage	V _R		1200	V	
Repetitive peak reverse voltage, T _J =25°C	V_{RRM}		1200	V	
Surge peak reverse voltage	V_{RSM}		1200	V	
Maximum DC forward current	I _F	T _C = 146°C	10	Α	
Non-repetitive forward surge current		$T_C = 25$ °C, $t_p = 10$ ms	120	А	
sine halfwave	I _{FSM}	$T_C = 110^{\circ}C, t_p = 10 ms$	110		
Repetitive forward surge current	1	$T_C = 25$ °C, $t_p = 10$ ms	39.4	Α	
sine halfwave, D=0.1	I _{FRM}	$T_C = 110^{\circ}C, t_p = 10 \text{ms}$	24		
Non-repetitive peak forward current		$T_C = 25^{\circ}C, t_p = 10 \mu s$	720		
	I _{F,max}	$T_C = 110^{\circ}C, t_p = 10\mu s$	720	Α	
.2.	∫i²dt	$T_C = 25$ °C, $t_p = 10$ ms	72	A^2s	
i ² t value		$T_C = 110^{\circ}C, t_p = 10 \text{ms}$	60		
Power dissipation	P _{tot}	T _C = 25°C	136.4	W	
		T _C = 146°C	26.4		
Maximum junction temperature	$T_{J,max}$		175	°C	
Operating and storage temperature	T _J , T _{STG}		-55 to 175	°C	
Soldering temperatures, wavesoldering only allowed at leads	T_{sold}	1.6mm from case for 10s	260	°C	

Thermal Characteristics

Parameter	Symbol	Test Conditions	Value			- Units
			Min	Тур	Max	Offics
Thermal resistance, junction-to-case	$R_{\theta JC}$			0.83	1.1	°C/W

Datasheet: UJ3D1210K2 Rev. C, Jan 2025 2











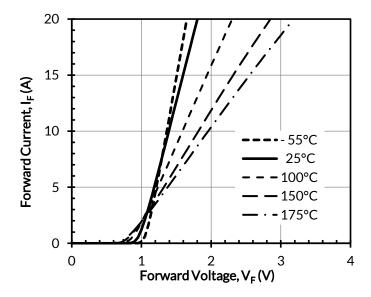


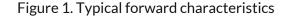
Electrical Characteristics (T_J = +25°C unless otherwise specified)

Parameter	Symbol	Test Conditions	Value			Units
			Min	Тур	Max	UIIILS
Forward voltage	V _F	I _F = 10A, T _J =25°C	-	1.4	1.6	V
		I _F = 10A, T _J = 150°C	-	1.85	2.3	
		I _F = 10A, T _J = 175°C	-	2	2.6	
Reverse current	I _R	V _R =1200V, T _J =25°C	-	10	110	μΑ
		V _R =1200V, T _J =175°C	-	450		
Total capacitive charge ⁽¹⁾	Q _C	V _R =800V		51		nC
Total capacitance	С	$V_R=1V, f=1MHz$		510		pF
		V _R =400V, f = 1MHz		48		
		V _R =800V, f = 1MHz		41		
Capacitance stored energy	E _C	V _R =800V		15		μЈ

(1) Q_c is independent on T_J , di_F/dt , and I_F as shown in the application note USCi_AN0011.

Typical Performance Diagrams





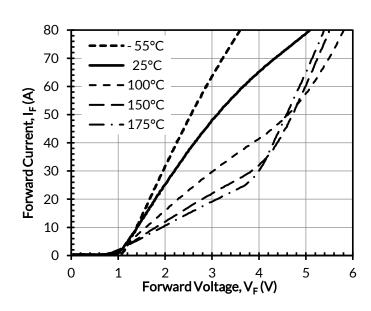


Figure 2. Typical forward characteristics in surge current



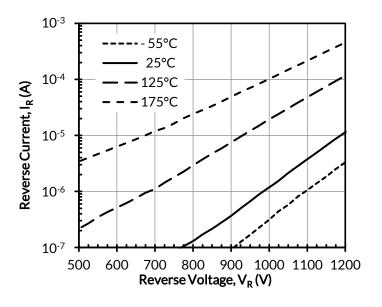








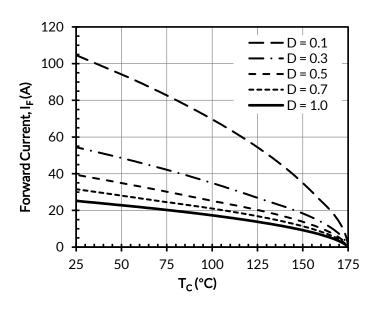




150 125 Power Disspiation, P_{Tot} (W) 100 75 50 25 0 50 100 25 75 125 150 175 T_C (°C)

Figure 3. Typical reverse characteristics

Figure 4. Power dissipation



Max. Thermal Impedance, $Z_{\theta JC}$ (°C/W) 1 D = 0.5D = 0.30.1 D = 0.1**--** D = 0.05 ···· D = 0.02 Single Pulse 0.01 1.E-05 1.E-04 1.E-03 1.E-02 1.E-01 Time, t(s)

Figure 5. Diode forward current

Figure 6. Maximum transient thermal impedance



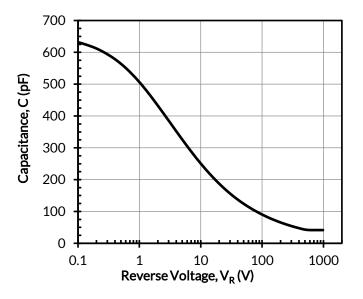












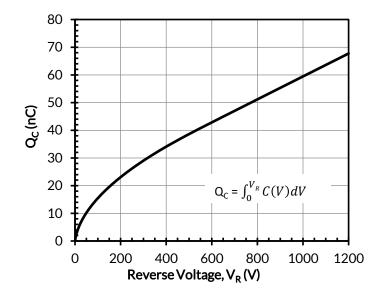


Figure 7. Capacitance vs. reverse voltage at 1MHz

Figure 8. Typical capacitive charge vs. reverse voltage

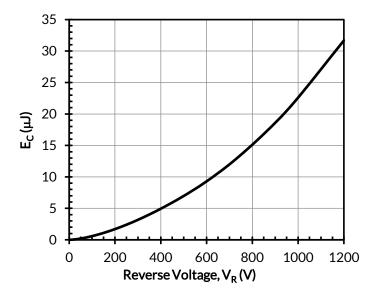


Figure 9. Typical capacitance stored energy vs. reverse voltage













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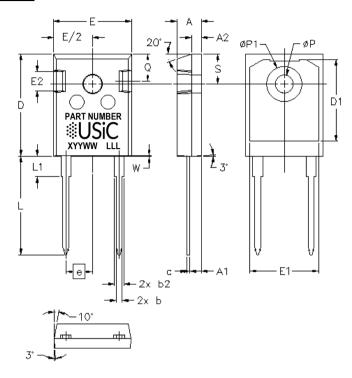
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TO-247-2L PACKAGE OUTLINE, PART MARKING AND TUBE SPECIFICATIONS

PACKAGE OUTLINE

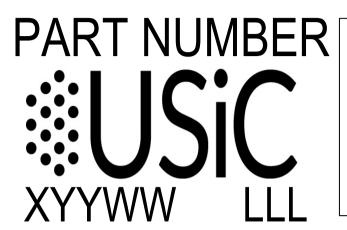


SYM	INCHES		MILLIMETERS			
	MIN	MAX	MIN	MAX		
Α	0.185	0.209	4.70	5.31		
A1	0.087	0.102	2.21	2.61		
A2	0.059	0.098	1.50	2.49		
b	0.039	0.055	0.99	1.40		
b2	0.065	0.094	1.65	2.39		
b4	0.102	0.135	2.59	3.43		
С	0.015	0.035	0.38	0.89		
D	0.819	0.845	20.80	21.46		
D1	0.515	-	13.08	-		
D2	0.02	0.053	0.51	1.35		
E	0.610	0.640	15.49	16.26		
е	0.214	0.214 BSC		.214 BSC 5.44 BSC		BSC
E1	0.530	-	13.46	-		
E2	0.135	0.157	3.43	3.99		
L	0.780	0.800	19.81	20.32		
L1	-	0.177	-	4.50		
ØΡ	0.140	0.144	3.56	3.66		
ØP1	0.278	0.291	7.06	7.39		
Q	0.212	0.244	5.39	6.20		
S	0.243	3 BSC	6.17 BSC			
W	-	0.006	-	0.15		



TO-247-2L PACKAGE OUTLINE, PART MARKING AND TUBE SPECIFICATIONS

PART MARKING



PART NUMBER = REFER TO
DS PN DECODER FOR DETAILS

X = ASSEMBLY SITE

YY = YEAR

WW = WORK WEEK

LLL = LOT ID

PACKING TYPE

ANTI-STATIC TUBE

QUANTITY /TUBE: 30 UNITS

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